

TPS59603-Q1 Synchronous Buck FET Driver for High-Frequency CPU Core Power in Automotive Applications

1 Features

- AEC-Q100 Qualified for Automotive Applications
 - Device Temperature Grade 1: -40°C to 125°C
 - Device Human Body Model ESD Classification Level H2
 - Device Charged Device Model ESD Classification Level C3B
- Reduced Dead-Time Drive Circuit for Optimized CCM
- Automatic Zero Crossing Detection for Optimized DCM Efficiency
- Multiple Low-Power Modes for Optimized Light-Load Efficiency
- Optimized Signal Path Delays for High-Frequency Operation
- Integrated BST Switch Drive Strength Optimized for low R_{dsON} FETs
- Optimized for 5-V FET Drive
- Conversion Input Voltage Range (V_{IN}): 2.5 to 28 V
- 2-mm × 2-mm, 8-Pin, WSON Thermal Pad Package with wettable flanks

2 Applications

- Automotive Rear Seat Entertainment (RSE) Tablets Using High-Frequency CPUs
- Automotive ADAS Processor Core Power

3 Description

The TPS59603-Q1 drivers are optimized for high-frequency CPU V_{CORE} applications. Advanced features such as reduced dead-time drive and auto zero crossing are used to optimize efficiency over the entire load range.

The $\overline{\text{SKIP}}$ pin provides the option of CCM operation to support controlled management of the output voltage. In addition, the TPS59603-Q1 supports two low-power modes. With the PWM input in tri-state, quiescent current is reduced to 130 μA , with immediate response. When $\overline{\text{SKIP}}$ is held at tri-state, the current is reduced to 8 μA (typically 20 μs is required to resume switching). Paired with the appropriate TI controller, the drivers deliver an exceptionally high performance power supply system.

The TPS59603-Q1 device is packaged in a space saving, thermally-enhanced 8-pin, 2-mm × 2-mm wettable flanks WSON package and operates from -40°C to 125°C .

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
TPS59603-Q1	WSON (8)	2.00 mm × 2.00 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Simplified Application

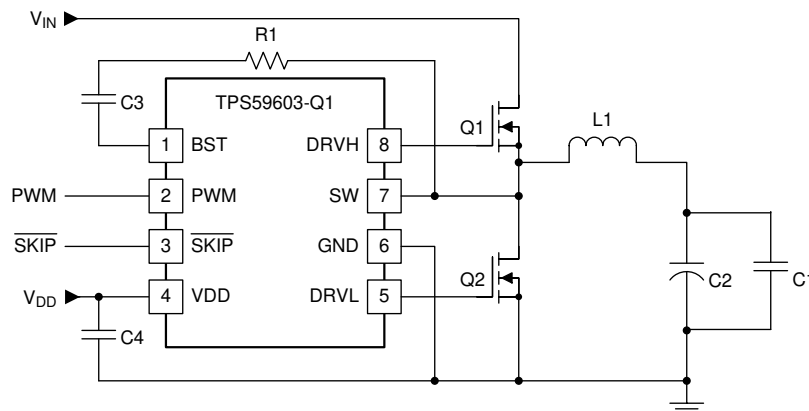


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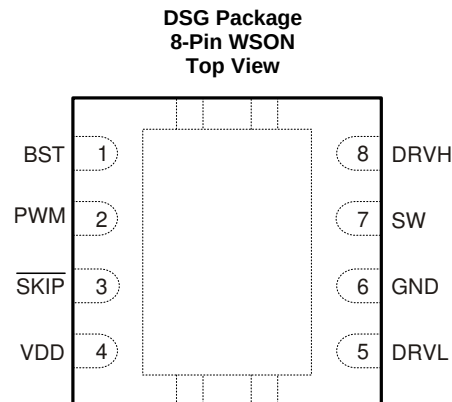
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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Original (January 2020) to Revision A	Page
• Changed hyperlink in Related Documentation section	14

5 Pin Configuration and Functions



Pin Functions

PIN		I/O ⁽¹⁾	DESCRIPTION
NAME	NO.		
BST	1	I	High-side N-channel FET bootstrap voltage input; power supply for high-side driver
DRVH	8	O	High-side N-channel gate drive output
DRVL	5	O	Synchronous low-side N-channel gate drive output
GND	6	G	Synchronous low-side N-channel gate drive return and device reference
PWM	2	I	PWM input. A tri-state voltage on this pin turns off both the high-side (DRVH) and low-side drivers (DRVL)
$\overline{\text{SKIP}}$	3	I	When $\overline{\text{SKIP}}$ is LO, the zero crossing comparator is active. The power chain enters discontinuous conduction mode when the inductor current reaches zero. When $\overline{\text{SKIP}}$ is HI, the zero crossing comparator is disabled, and the driver outputs follow the PWM input. A tri-state voltage on $\overline{\text{SKIP}}$ puts the driver into a very-low power state.
SW	7	I/O	High-side N-channel gate drive return. Also, zero-crossing sense input
VDD	4	I	5-V power supply input; decouple to GND with a ceramic capacitor with a value of 1 μF or greater
Thermal Pad		G	Tie to system GND plane with multiple vias

(1) I = Input, O = Output, G = Ground

6 Specifications

6.1 Absolute Maximum Ratings^{(1) (2)}

over operating free-air temperature (unless otherwise noted)

		MIN	MAX	UNIT
Input voltage	VDD	−0.3	6	V
	PWM, $\overline{\text{SKIP}}$	−0.3	6	
Output voltage	BST	−0.3	35	V
	BST (transient <20 ns)	−0.3	38	
	BST to SW; DRVH to SW	−0.3	6	
	SW	−2	30	
	DRVH, SW (transient <20 ns)	−5	38	
	DRVL	−0.3	6	
Ground pins	GND to PAD	−0.3	0.3	V
Operating junction temperature, T_J		−40	125	°C
Storage temperature range, T_{stg}		−55	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) All voltage values are with respect to the network ground terminal unless otherwise noted.

6.2 ESD Ratings

		VALUE	UNIT
$V_{\text{(ESD)}}$ Electrostatic discharge	Human body model (HBM), per AEC Q100-002 ⁽¹⁾	±2000	V
	Charged device model (CDM), per AEC Q100-011	±750	

- (1) AEC Q100-002 indicates HBM stressing is done in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

6.3 Recommended Operating Conditions

Over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
Input voltage	VDD	4.5	5	5.5	V
	PWM, $\overline{\text{SKIP}}$	−0.1		5.5	
Output voltage	BST	−0.1		34	V
	BST to SW; DRVH to SW	−0.1		5.5	
	SW	−1		28	
	DRVL	−0.1		5.5	
Ground pins	GND to PAD	−0.1		0.1	V
Operating junction temperature, T_J		−40		125	°C

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		TPS59603-Q1	UNIT
		WSN (DSG)	
		8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	63.1	°C/W
$R_{\theta JC(\text{top})}$	Junction-to-case (top) thermal resistance	74.1	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	34.3	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	2.0	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	34.9	°C/W
$R_{\theta JC(\text{bot})}$	Junction-to-case (bottom) thermal resistance	11.7	°C/W

- (1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report (SPRA953).

6.5 Electrical Characteristics

These specifications apply for $-40^{\circ}\text{C} \leq T_J \leq 125^{\circ}\text{C}$, and $V_{\text{VDD}} = 5\text{ V}$ unless otherwise specified.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
VDD INPUT SUPPLY						
I _{CC}	Supply current (operating)	$V_{\overline{\text{SKIP}}} = V_{\text{VDD}}$ or $V_{\overline{\text{SKIP}}} = 0\text{ V}$, PWM = High		160	600	μA
		$V_{\overline{\text{SKIP}}} = V_{\text{VDD}}$ or $V_{\overline{\text{SKIP}}} = 0\text{ V}$, PWM = Low		250		
		$V_{\overline{\text{SKIP}}} = V_{\text{VDD}}$ or $V_{\overline{\text{SKIP}}} = 0\text{ V}$, PWM = Float		130		
		$V_{\overline{\text{SKIP}}} = \text{Float}$		8		
VDD UNDERVOLTAGE LOCKOUT (UVLO)						
V _{UVLO}	UVLO threshold	Rising threshold			4.19	V
		Falling threshold	3.65			
V _{UVHYS}	UVLO hysteresis			0.2		V
PWM AND $\overline{\text{SKIP}}$ I/O SPECIFICATIONS						
R _I	Input impedance	Pullup to VDD		1.7		MΩ
		Pulldown (to GND)		800		kΩ
V _{IL}	Low-level input voltage				0.6	V
V _{IH}	High-level input voltage		2.70			V
V _{IHH}	Hysteresis			0.2		V
V _{TS}	Tri-state voltage		1.3		2.0	V
t _{THOLD(off1)}	Tri-state activation time (falling) PWM			60		ns
t _{THOLD(off2)}	Tri-state activation time (rising) PWM			60		ns
t _{TSKF}	Tri-state activation time (falling) $\overline{\text{SKIP}}$			1		μs
t _{TSKR}	Tri-state activation time (rising) $\overline{\text{SKIP}}$			1		μs
t _{3RD(PWM)}	Tri-state exit time PWM				100	ns
t _{3RD($\overline{\text{SKIP}}$)}	Tri-state exit time $\overline{\text{SKIP}}$				50	μs
HIGH-SIDE GATE DRIVER (DRVH)						
t _{R(DRVH)}	Rise time	DRVH rising, C _{DRVH} = 3.3 nF; 20% to 80%		30		ns
t _{RPD(DRVH)}	Rise time propogation delay	C _{DRVH} = 3.3 nF		40		ns
R _{SRC}	Source resistance	Source resistance, (V _{BST} – V _{SW}) = 5 V, high state, (V _{BST} – V _{DRVH}) = 0.1 V		2	4	Ω
t _{F(DRVH)}	Fall time	DRVH falling, C _{DRVH} = 3.3 nF		8		ns
t _{FPD(DRVH)}	Fall-time propagation delay	C _{DRVH} = 3.3 nF		25		ns
R _{SNK}	Sink resistance	Sink resistance, (V _{BST} – V _{SW}) forced to 5 V, low state (V _{DRVH} – V _{SW}) = 0.1 V		0.5	1.6	Ω
R _{DRVH}	DRVH to SW resistance ⁽¹⁾			100		kΩ

(1) Specified by design. Not production tested.

Electrical Characteristics (continued)

These specifications apply for $-40^{\circ}\text{C} \leq T_J \leq 125^{\circ}\text{C}$, and $V_{\text{VDD}} = 5\text{ V}$ unless otherwise specified.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
LOW-SIDE GATE DRIVER (DRV_L)						
$t_{\text{R(DRV_L)}}$	Rise time	DRV_L rising, $C_{\text{DRV_L}} = 3.3\text{ nF}$; 20% to 80%		15		ns
$t_{\text{RPD(DRV_L)}}$	Rise time propagation delay	$C_{\text{DRV_L}} = 3.3\text{ nF}$		35		ns
R_{SRC}	Source resistance	Source resistance, $(V_{\text{VDD}} - \text{GND}) = 5\text{ V}$, high state, $(V_{\text{VDD}} - V_{\text{DRV_L}}) = 0.1\text{ V}$		1.5	3	Ω
$t_{\text{F(DRV_L)}}$	Fall time	DRV_L falling, $C_{\text{DRV_L}} = 3.3\text{ nF}$		10		ns
$t_{\text{FPD(DRV_L)}}$	Fall-time propagation delay	$C_{\text{DRV_L}} = 3.3\text{ nF}$		15		ns
R_{SNK}	Sink resistance	Sink resistance, $(V_{\text{VDD}} - \text{GND}) = 5\text{ V}$, low state, $(V_{\text{DRV_L}} - \text{GND}) = 0.1\text{ V}$		0.4	1.6	Ω
$R_{\text{DRV_L}}$	DRV_L to GND resistance ⁽¹⁾			100		k Ω
GATE DRIVER DEAD-TIME						
$t_{\text{R(DT)}}$	Rising edge		0	20	40	ns
$t_{\text{F(DT)}}$	Falling edge		0	10	25	ns
ZERO CROSSING COMPARATOR						
V_{ZX}	Zero crossing offset	SW voltage rising	-2.25	0	2.00	mV
BOOTSTRAP SWITCH						
V_{FBST}	Forward voltage	$I_{\text{F}} = 10\text{ mA}$		120	240	mV
I_{RLEAK}	Reverse leakage	$(V_{\text{BST}} - V_{\text{VDD}}) = 25\text{ V}$			2	μA
$R_{\text{DS(on)}}$	On-resistance			12	24	Ω

6.6 Typical Characteristics

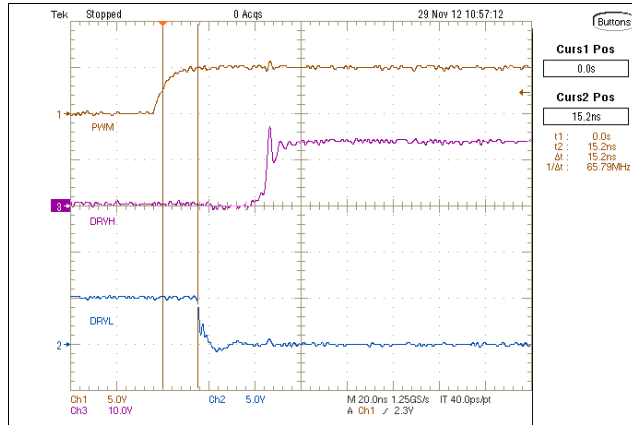


Figure 1. PWM High to DRVH Low

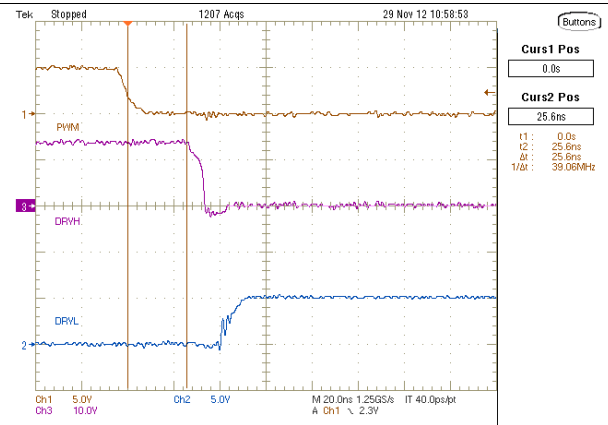


Figure 2. PWM Low to DRVH Low

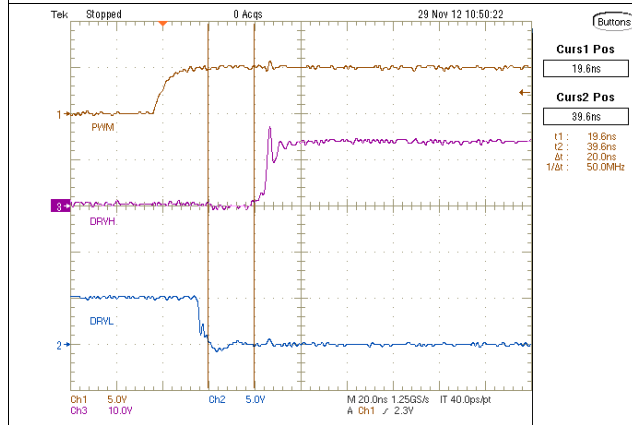


Figure 3. DRVH Low to DRVH High

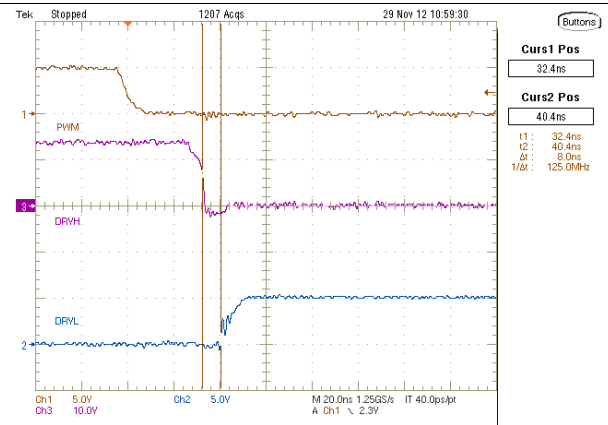


Figure 4. DRVH Low to DRVH High

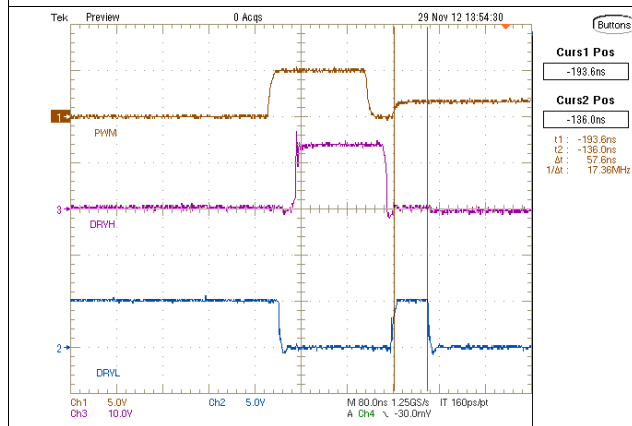


Figure 5. PWM Low to Tri-State

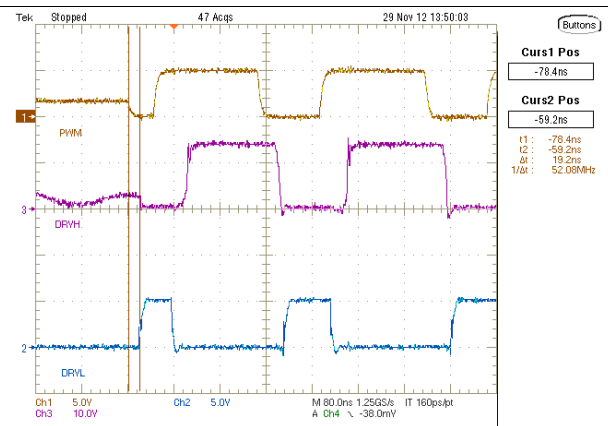


Figure 6. PWM Tri-State to Low

Typical Characteristics (continued)

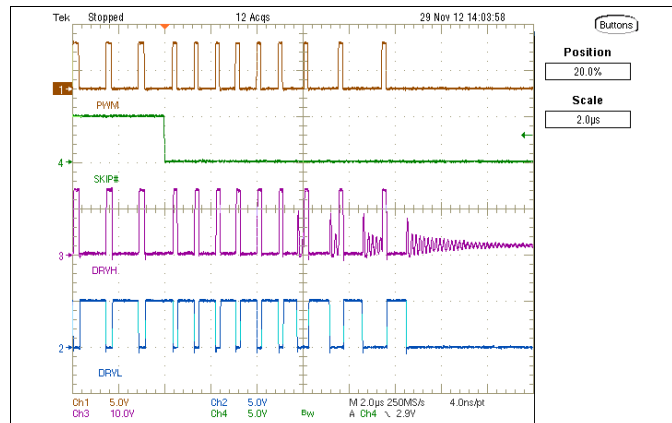


Figure 7. SKIP Mode Entry

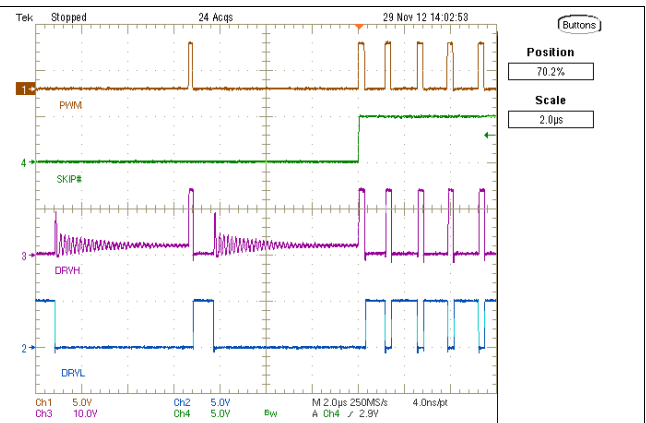


Figure 8. SKIP Mode Exit

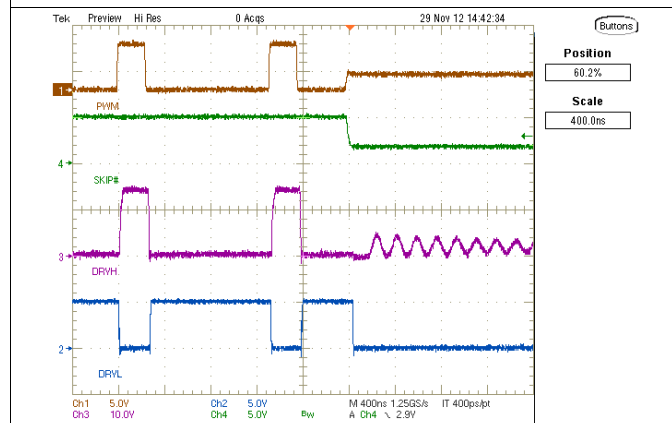


Figure 9. Very-Low-Power Mode Entry

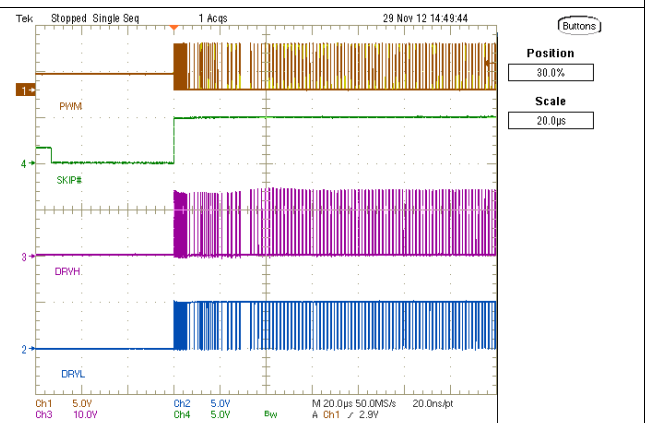
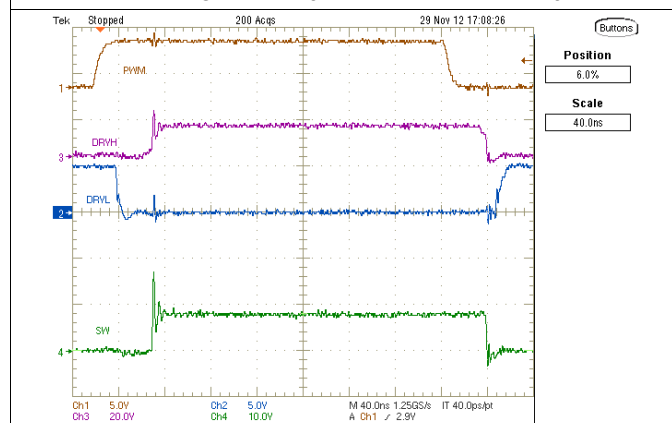
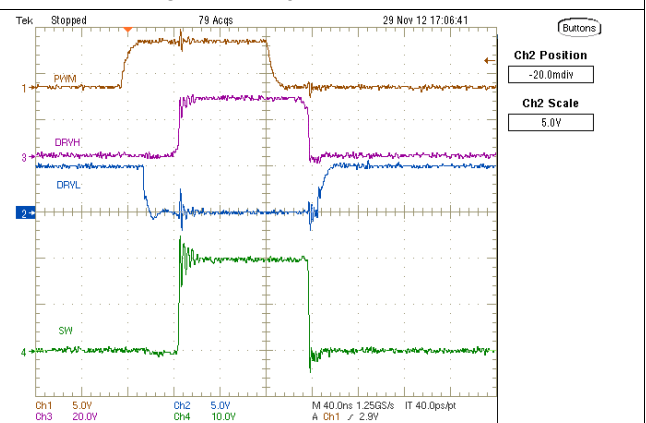


Figure 10. Very-Low-Power Mode Exit



$V_{IN} = 8V$

Figure 11. SW Node-Ringing



$V_{IN} = 20V$

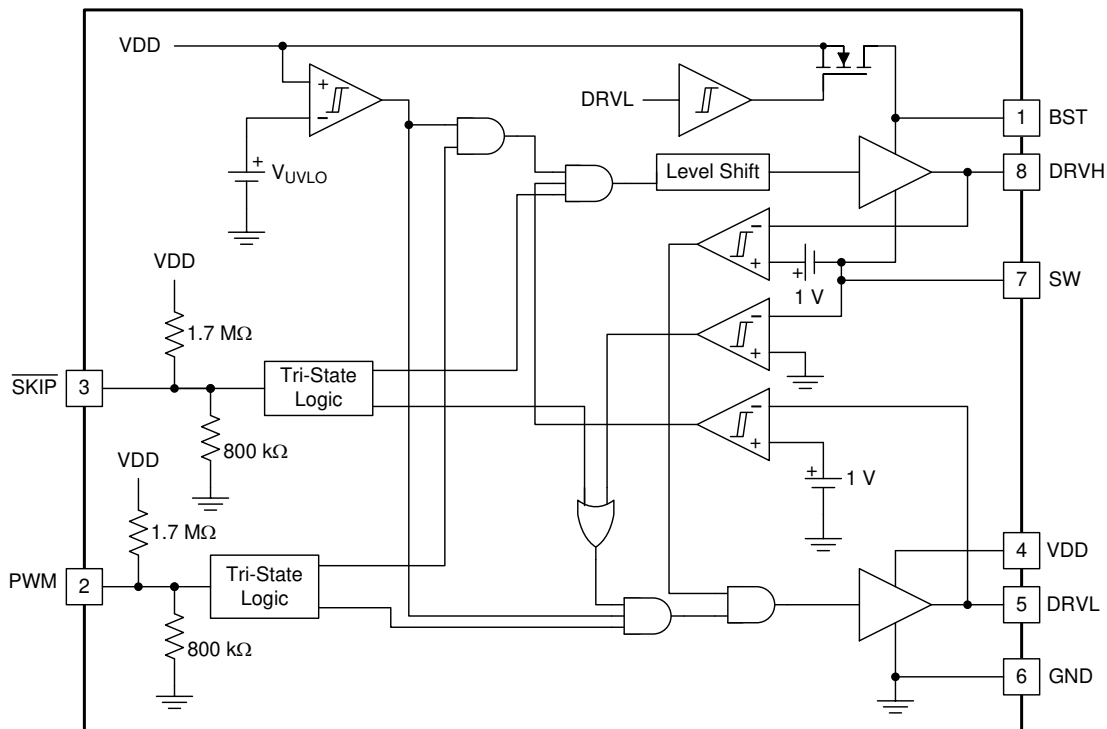
Figure 12. SW Node-Ringing

7 Detailed Description

7.1 Overview

The TPS59603-Q1 device is a synchronous-buck MOSFET driver designed to drive both high-side and low-side MOSFETs. It allows high-frequency operation with current driving capability matched to the application. The integrated boost switch is internal. The TPS59603-Q1 device employs dead-time reduction control and shoot-through protection, which helps avoid simultaneous conduction of high-side and low-side MOSFETs. Also, the drivers improve light-load efficiency with integrated DCM-mode operation using adaptive crossing detection. Typical applications yield a steady-state duty cycle of 60% or less. For high steady-state duty cycle applications, including a small external Schottky diode may help to ensure sufficient charging of the bootstrap capacitor.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 UVLO Protection

The UVLO comparator evaluates the VDD voltage level. As V_{VDD} rises, both DRVH and DRVL hold actively low at all times until V_{VDD} reaches the higher UVLO threshold (V_{UVLO_H}). Then, the driver becomes operational and responds to PWM and SKIP commands. If VDD falls below the lower UVLO threshold ($V_{UVLO_L} = V_{UVLO_H} - \text{Hysteresis}$), the device disables the driver and drives the outputs of DRVH and DRVL actively low. Figure 13 shows this function.

CAUTION

Do not start the driver in the very low power mode ($\overline{\text{SKIP}}$ = Tri-state).

Feature Description (continued)

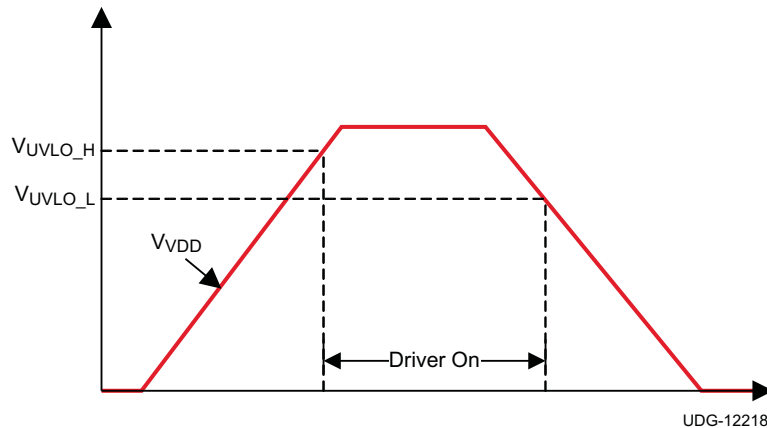


Figure 13. UVLO Operation

7.3.2 PWM Pin

The PWM pin incorporates an input tri-state function. The device forces the gate driver outputs to low when PWM is driven into the tri-state window and the driver enters a low power state with zero exit latency. The pin incorporates a weak pullup to maintain the voltage within the tri-state window during low-power modes. Operation into and out of a tri-state condition follows the timing diagram outlined in Figure 14.

When V_{DD} reaches the UVLO_H level, a tri-state voltage range (window) is set for the PWM input voltage. The window is defined as the PWM voltage range between PWM logic high (V_{IH}) and logic low (V_{IL}) thresholds. The device sets high-level input voltage and low-level input voltage threshold levels to accommodate both 3.3-V (typical) and 5-V (typical) PWM drive signals.

When the PWM exits the tri-state condition, the driver enters CCM for a period of 4 μs, regardless of the state of the SKIP pin. Typical operation requires this time period in order for the auto-zero comparator to resume.

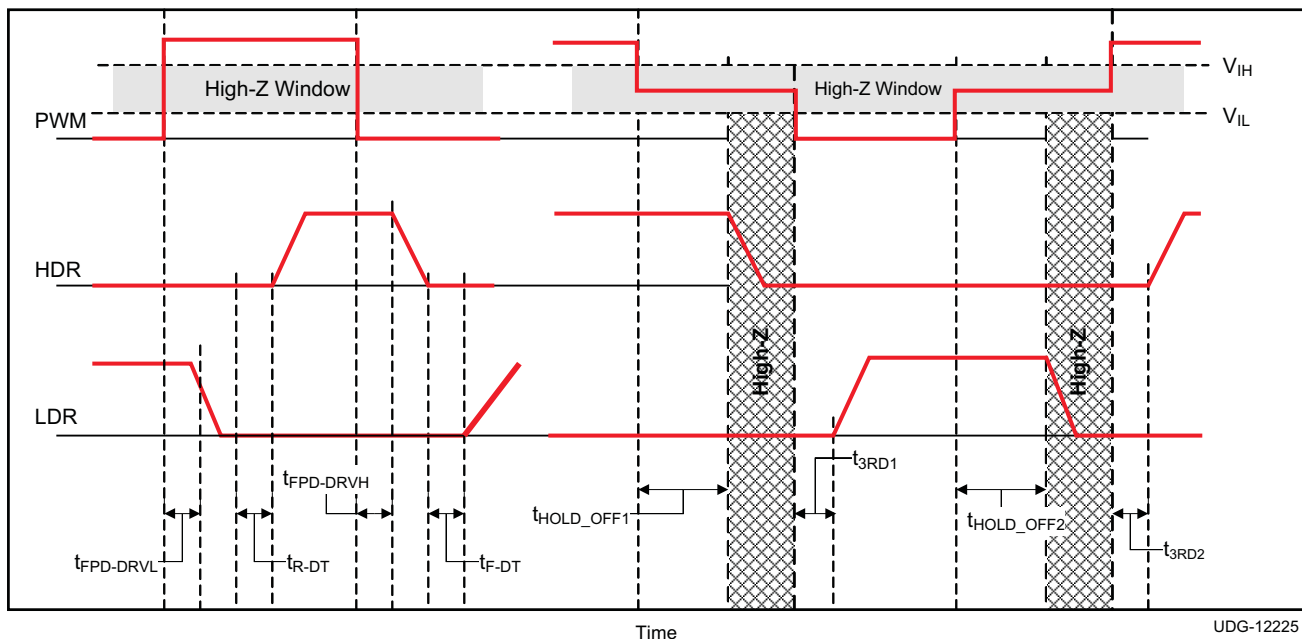


Figure 14. PWM Tri-State Timing Diagram

Feature Description (continued)

7.3.3 $\overline{\text{SKIP}}$ Pin

The $\overline{\text{SKIP}}$ pin incorporates the input tri-state buffer as PWM. The function is somewhat different. When $\overline{\text{SKIP}}$ is low, the zero crossing (ZX) detection comparator is enabled, and DCM mode operation occurs if the load current is less than the critical current. When $\overline{\text{SKIP}}$ is high, the ZX comparator disables, and the converter enters FCCM mode. When the $\overline{\text{SKIP}}$ pin is in a tri-state condition, typical operation forces the gate driver outputs low and the driver enters a very-low-power state. In the low-power state, the UVLO comparator remains off to reduce quiescent current. When the $\overline{\text{SKIP}}$ pin voltage is pulled either low or high, the driver wakes up and is able to accept PWM pulses in less than 50 μs .

Table 1 shows the logic functions of UVLO, PWM, $\overline{\text{SKIP}}$, DRVH, and DRVL.

Table 1. Logic Functions

UVLO	PWM	$\overline{\text{SKIP}}$	DRVL	DRVH	MODE
Active	—	—	Low	Low	Disabled
Inactive	Low	Low	High ⁽¹⁾	Low	DCM ⁽¹⁾
Inactive	Low	High	High	Low	FCCM
Inactive	High	H or L	Low	High	
Inactive	Tri-state	H or L	Low	Low	Low power
Inactive	—	Tri-state	Low	Low	Very-low power

(1) Until zero crossing protection occurs.

7.3.3.1 Zero Crossing (ZX) Operation

The zero crossing comparator is adaptive for improved accuracy. As the output current decreases from a heavy load condition, the inductor current also reduces and eventually arrives at a *valley*, where it touches zero current, which is the boundary between continuous conduction and discontinuous conduction modes. The SW pin detects the zero-current condition. When this zero inductor current condition occurs, the ZX comparator turns off the rectifying MOSFET.

7.3.4 Adaptive Dead-Time Control and Shoot-Through Protection

The driver utilizes an anti-shoot-through and adaptive dead-time control to minimize low-side body diode conduction time and maintain high efficiency. When the PWM input voltage becomes high, the low-side MOSFET gate voltage begins to fall after a propagation delay. At the same time, DRVL voltage is sensed, and high-side driving voltage starts to increase after DRVL voltage is lower than a proper threshold.

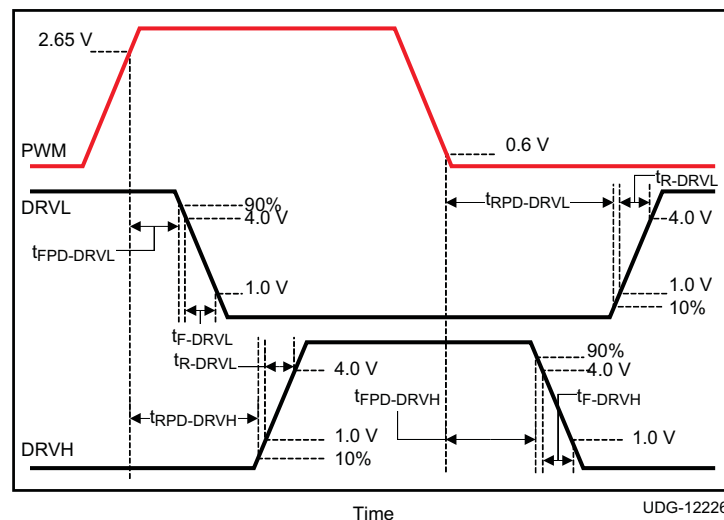


Figure 15. Rise and Fall Timing and Propagation Delay Definitions

Typical operation manages to near zero the dead-time between the low-side gate turn-off to high-side gate voltage turn-on, and high-side gate turn-off to low-side gate turn-on, in order to avoid simultaneous conduction of both MOSFETs, as well as to reduce body diode conduction and recovery losses. This operation also reduces ringing on the leading edge of the SW waveform.

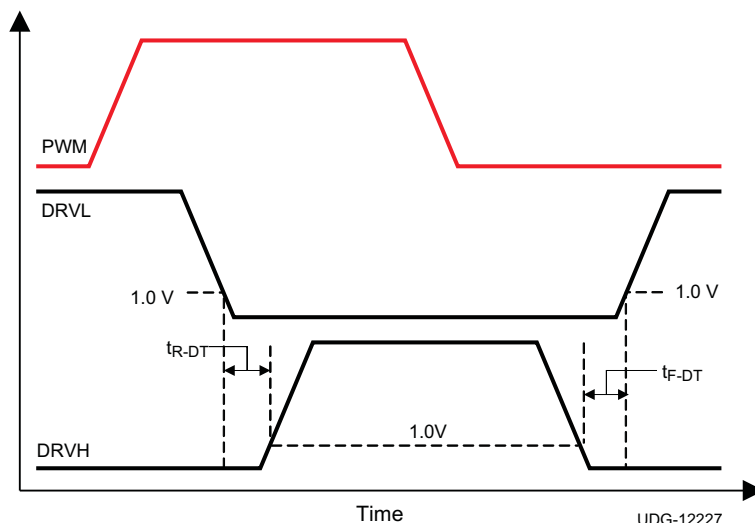


Figure 16. Dead-Time Definitions

7.3.5 Integrated Boost-Switch

To maintain a BST-SW voltage close to VDD (to get lower conduction losses on the high-side FET), the conventional diode between the VDD pin and BST pin is replaced by a FET, which is gated by the DRVL signal.

7.4 Device Functional Modes

The TPS59603-Q1 device operates in CCM mode when the $\overline{\text{SKIP}}$ pin is high, and it enters DCM mode when the $\overline{\text{SKIP}}$ pin is low. When both the $\overline{\text{SKIP}}$ pin and the PWM pin are in a tri-state condition, it forces the gate driver outputs low and the driver enters a very-low-power state.

8 Power Supply Recommendations

The voltage range for the VDD pin is between 4.5 V and 5.5 V. A 5-V power supply is recommended for the VDD pin of the TPS59603-Q1 device.

9 Layout

9.1 Layout Guidelines

To improve the switching characteristics and design efficiency, these layout rules must be considered:

- Locate the driver as close as possible to the MOSFETs.
- Locate the VDD and bootstrap capacitors as close as possible to the driver.
- Pay special attention to the GND trace. Use the thermal pad of the package as the GND by connecting it to the GND pin. The GND trace or pad from the driver goes directly to the source of the MOSFET, but should not include the high current path of the main current flowing through the drain and source of the MOSFET.
- Use a similar rule for the switch-node as for the GND.
- Use wide traces for DRVH and DRVL closely following the related SW and GND traces. A width of between 80 and 100 mils is preferable where possible.
- Place the bypass capacitors as close as possible to the driver.
- Avoid PWM and enable traces going close to the SW and pad where high dV/dT voltage can induce significant noise into the relatively high-impedance leads.

A poor layout can decrease the reliability of the entire system.

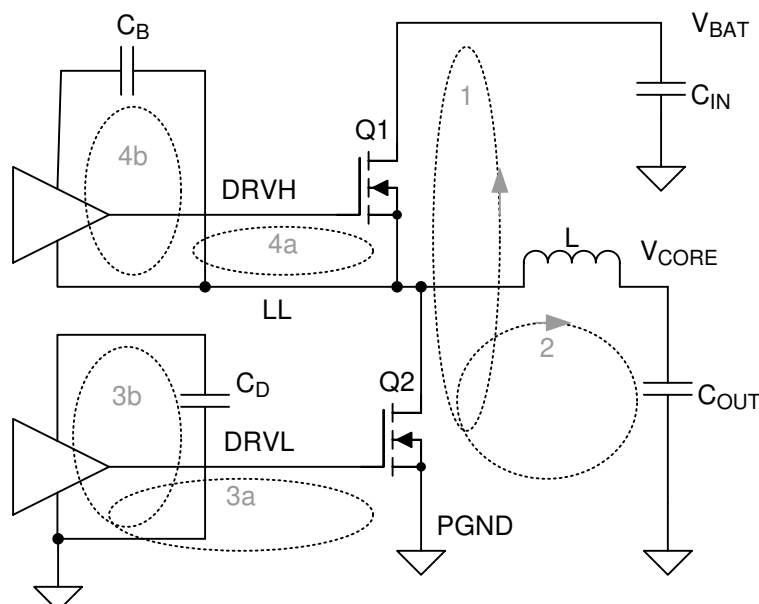
9.2 Layout Recommendation

Figure 17 above shows the primary current loops in each phase, numbered in order of importance.

The most important loop to minimize the area of is loop 1, the path from the input capacitor through the high and low-side FETs, and back to the capacitor through ground.

Loop 2 is from the inductor through the output capacitor, ground, and Q2. The layout of the low-side gate drive (Loops 3a and 3b) is important. The guidelines for the gate drive layout are:

- Make the low-side gate drive length as short as possible (1 inch or less preferred).
- Make the DRVL width to length ratio of 1:10, wider (1:5) if possible.
- If changing layers is necessary, use at least two vias.



UDG-12191

Figure 17. Layout recommendations to minimize major Current loops

10 Device and Documentation Support

10.1 Device Support

10.1.1 Development Support

For the Power Stage Designer, go to [Power Stage Designer™ Tool of Most Commonly Used Switch-mode Power Supplies](#)

10.2 Documentation Support

10.2.1 Related Documentation

[TPS59632-Q1 2.5-V To 24-V, 3-, 2-, and 1-Phase Step-Down Driverless Controller for Automotive ADAS Applications](#) data sheet

10.3 Community Resources

TI E2E™ [support forums](#) are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

10.4 Trademarks

E2E is a trademark of Texas Instruments.

10.5 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

10.6 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
TPS59603QDSGRQ1	Active	Production	WSO (DSG) 8	3000 LARGE T&R	Yes	SN	Level-2-260C-1 YEAR	-40 to 125	603Q
TPS59603QDSGRQ1.A	Active	Production	WSO (DSG) 8	3000 LARGE T&R	Yes	SN	Level-2-260C-1 YEAR	-40 to 125	603Q
TPS59603QDSGTQ1	Active	Production	WSO (DSG) 8	250 SMALL T&R	Yes	SN	Level-2-260C-1 YEAR	-40 to 125	603Q
TPS59603QDSGTQ1.A	Active	Production	WSO (DSG) 8	250 SMALL T&R	Yes	SN	Level-2-260C-1 YEAR	-40 to 125	603Q

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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GENERIC PACKAGE VIEW

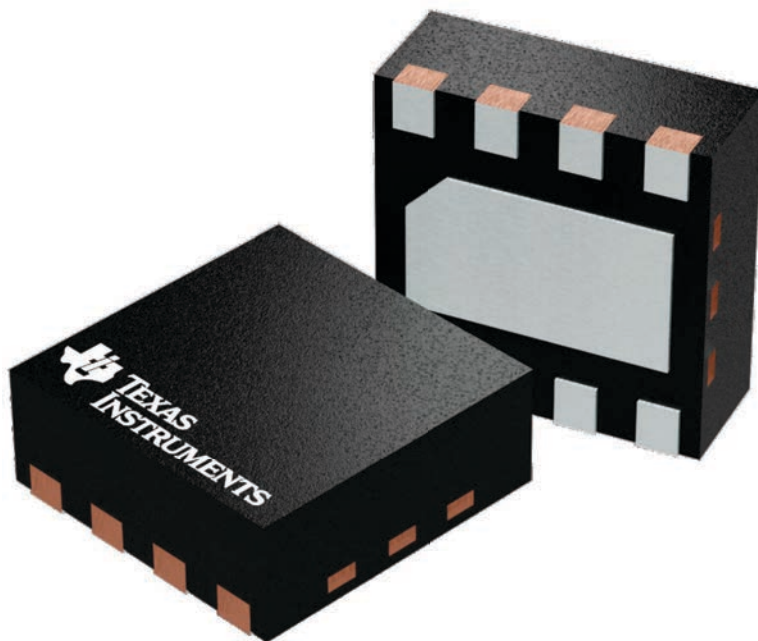
DSG 8

WSON - 0.8 mm max height

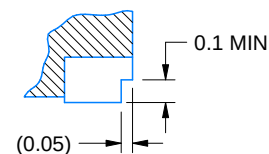
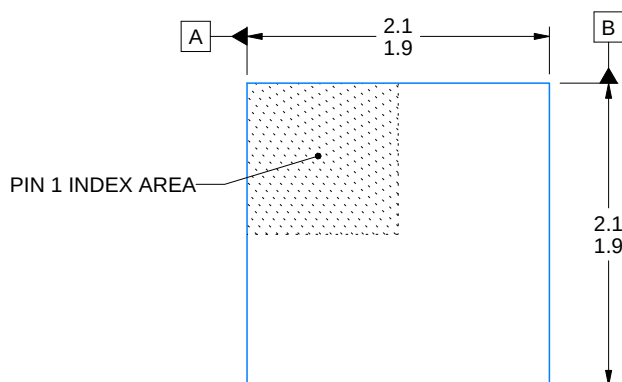
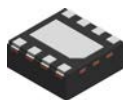
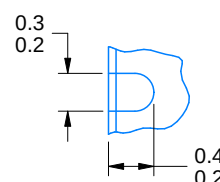
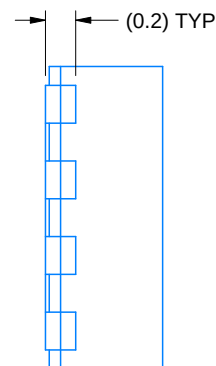
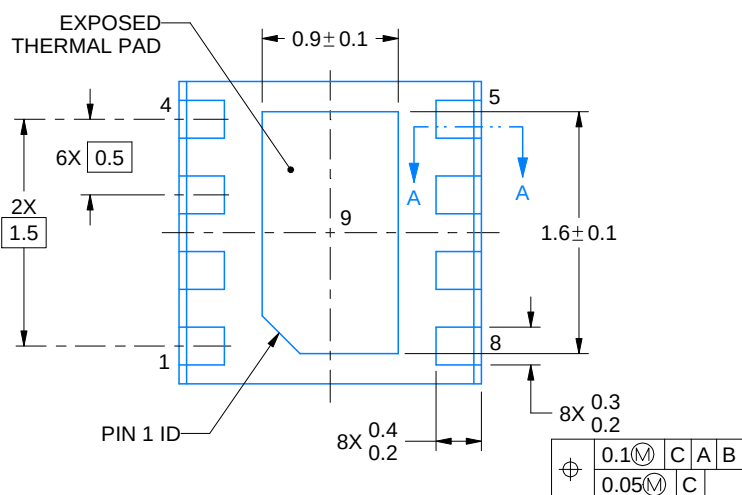
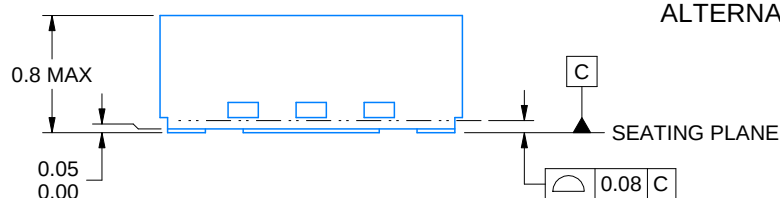
2 x 2, 0.5 mm pitch

PLASTIC SMALL OUTLINE - NO LEAD

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



4224783/A

SECTION A-A
TYPICALALTERNATIVE TERMINAL SHAPE
TYPICAL

⌀	0.1(M)	C	A	B
	0.05(M)	C		

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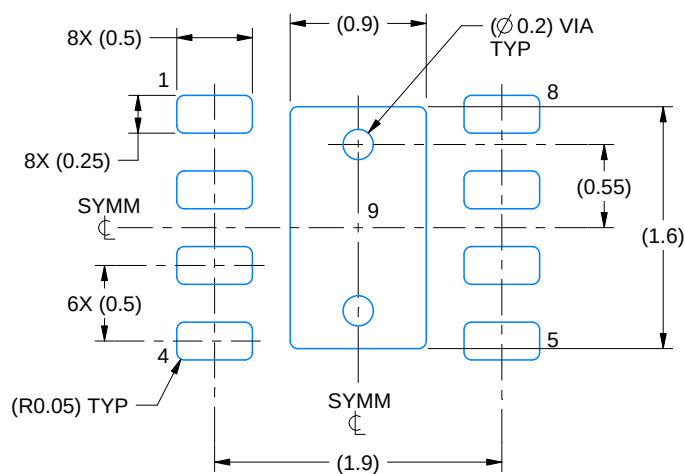
NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

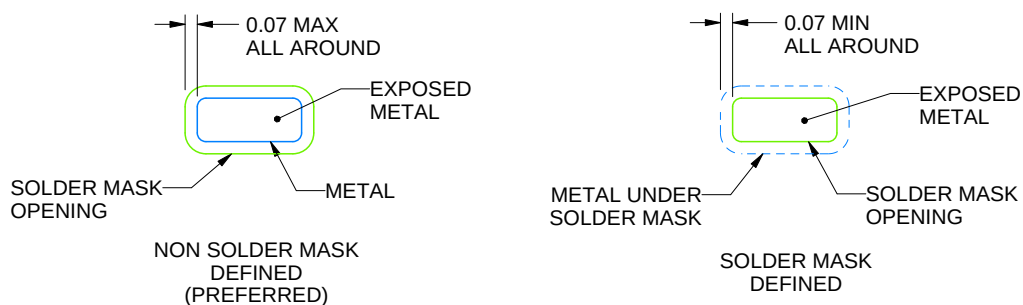
DSG0008B

WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:20X



SOLDER MASK DETAILS

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NOTES: (continued)

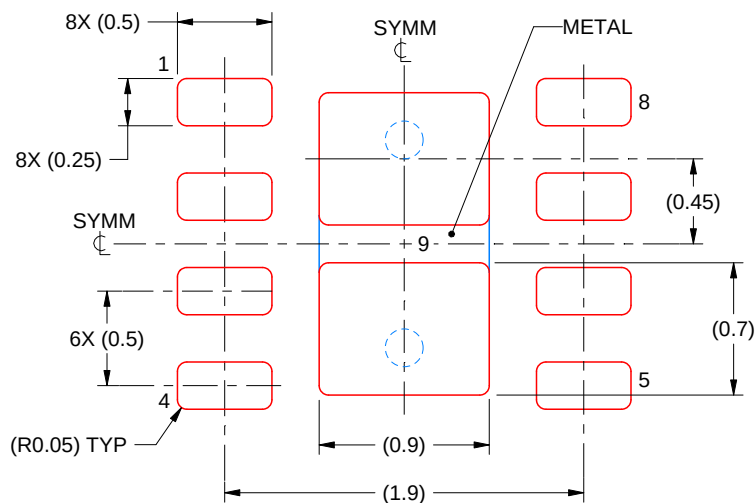
4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

EXAMPLE STENCIL DESIGN

DSG0008B

WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD 9:
87% PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE
SCALE:25X

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NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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